

AMENDED AND NEW CLAIMS FOR SERIAL NO. 09/847,622

1. (Twice Amended) A transistor, comprising:

a substrate;

an active region defined in said substrate;

a gate insulation layer formed above said active region; and

a gate electrode formed above said gate insulation layer, said gate electrode having a middle portion located over the active region, said middle portion having an extension of an upper part along the gate length direction that decreases from bottom to top of the upper part, and said middle portion also having a gate length and a gate height, wherein a cross-sectional area of said gate electrode in a plane defined by said gate length and said gate height of the middle portion exceeds a value obtained by multiplying the gate length by the gate height.

27. (Amended) A transistor, comprising:

a substrate;

a gate insulation layer formed above said substrate; and

a gate electrode formed above said gate insulation layer, said gate electrode having an upper portion comprised of polysilicon and a lower portion, said upper portion having a plurality of extensions formed thereon, said extensions of said upper portion extending laterally beyond said lower portion of said gate electrode